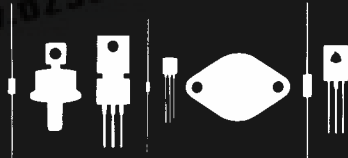


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145 Adams Avenue  
Hauppauge, New York 11788



MJE370 PNP  
MJE520 NPN

SILICON COMPLEMENTARY  
POWER TRANSISTORS

JEDEC TO-126 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR MJE370, MJE520 types are Complementary Silicon Power Transistors designed for use in general purpose amplifier and switching applications.

MAXIMUM RATINGS (T<sub>C</sub>=25°C)

	SYMBOL		UNIT
Collector-Base Voltage	V <sub>CB0</sub>	30	V
Collector-Emitter Voltage	V <sub>CEO</sub>	30	V
Emitter-Base Voltage	V <sub>EB0</sub>	4.0	V
Collector Current	I <sub>C</sub>	3.0	A
Collector Current (PEAK)	I <sub>CM</sub>	7.0	A
Power Dissipation	P <sub>D</sub>	25	W
Operating and Storage Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 TO +150	°C
Thermal Resistance	θ <sub>JC</sub>	5.0	°C/W

ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I <sub>CB0</sub>	V <sub>CB</sub> =30V		100	μA
I <sub>EB0</sub>	V <sub>EB</sub> =4.0V		100	μA
BV <sub>CEO</sub>	I <sub>C</sub> =100mA	30		V
h <sub>FE</sub>	V <sub>CE</sub> =1.0V, I <sub>C</sub> =1.0A	25		

**Central™  
Semiconductor Corp.**

145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110 • Fax: (631) 435-1824  
www.centrasemi.com

